Silicon N-Channel MOS FET

# HITACHI

ADE-208-1302 (Z) 1st. Edition Mar. 2001

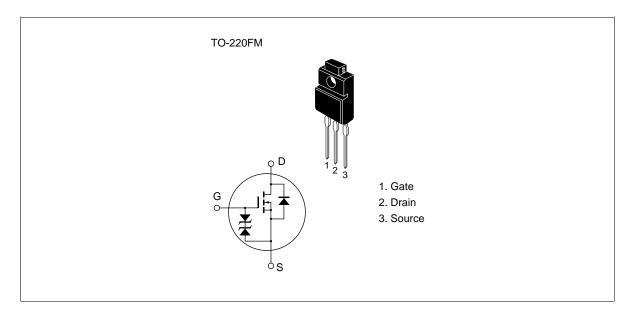
## Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

### Outline





# Absolute Maximum Ratings (Ta = $25^{\circ}$ C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1626	V <sub>DSS</sub>	450	V
	2SK1627		500	
Gate to source voltage		V <sub>GSS</sub>	±30	V
Drain current		I <sub>D</sub>	5	A
Drain peak current		L *1 D(pulse)	20	A
Body to drain diode reverse	e drain current	I <sub>DR</sub>	5	A
Channel dissipation		Pch*2	35	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Note 1. PW 10 µs, duty cycle 1%

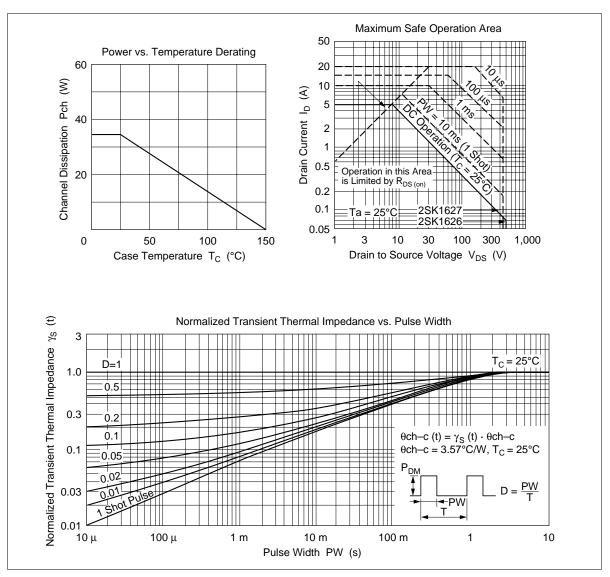
2. Value at  $T_c = 25^{\circ}C$ 

## **Electrical Characteristics** (Ta = 25°C)

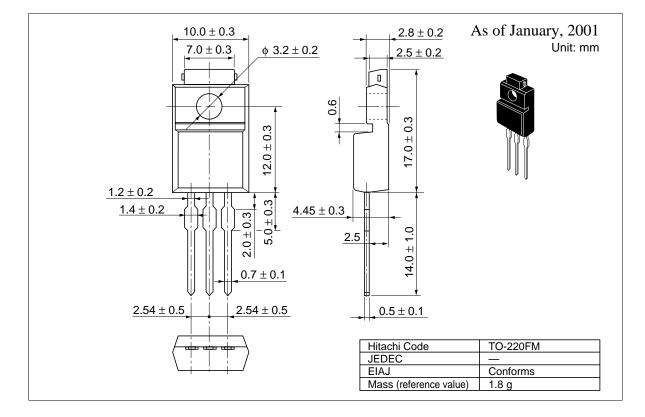
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1626	$V_{(BR)DSS}$	450	_	_	V	$I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$
breakdown voltage	2SK1627	-	500	=			
Gate to source breakdown voltage		$V_{(\text{BR})\text{GSS}}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I <sub>GSS</sub>	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage	2SK1626	I <sub>DSS</sub>	—	—	250	μA	$V_{\rm DS} = 360 \ V, \ V_{\rm GS} = 0$
drain current	2SK1627	-					$V_{\rm DS} = 400 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage		$V_{\text{GS(off)}}$	2.0	—	3.0	V	$I_{\rm D}$ = 1 mA, $V_{\rm DS}$ = 10 V
Static Drain to source	e 2SK1626	$R_{DS(on)}$	_	1.0	1.4		$I_{\rm D} = 2.5 \text{ A}, \text{ V}_{\rm GS} = 10 \text{ V}^{*1}$
on state resistance	2SK1627	-	—	1.2	1.5	_	
Forward transfer adm	nittance	yfs	2.5	4.0	—	S	$I_{\rm D}$ = 2.5 A, $V_{\rm DS}$ = 10 V * <sup>1</sup>
Input capacitance		Ciss		640		pF	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0,$
Output capacitance		Coss	_	160	_	pF	f = 1 MHz
Reverse transfer capacitance		Crss	_	20	_	pF	
Turn-on delay time		$\mathbf{t}_{d(on)}$	_	10	_	ns	$I_{\rm D} = 2.5 \text{ A}, V_{\rm GS} = 10 \text{ V},$
Rise time		t,	_	25	_	ns	R <sub>L</sub> = 12
Turn-off delay time		$t_{d(off)}$	—	50	—	ns	
Fall time		t <sub>f</sub>	_	30	_	ns	
Body to drain diode for voltage	orward	$V_{DF}$	_	0.95	_	V	$I_{F} = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time		t <sub>rr</sub>	_	300	_	ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$
Note 1 Pulse test	t						

Note 1. Pulse test

See characteristic curves of 2SK1155, 2SK1156.



### **Package Dimensions**



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